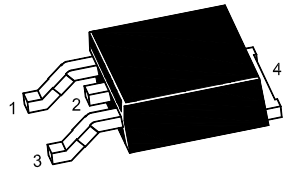
2SA1718R-HAF

PNP Silicon Epitaxial Planar Transistor

for power switching and amplifier applications



1. Base 2. Collector 3. Emitter 4. Collector
TO-252 Plastic Package

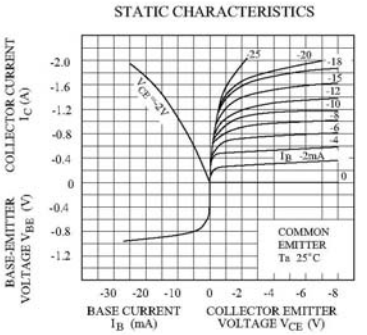
Absolute Maximum Ratings (T_a = 25 °C)

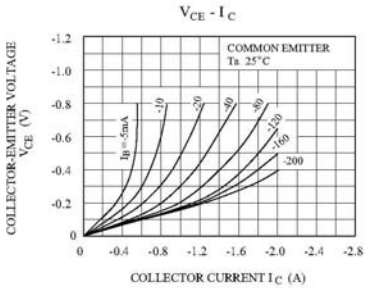
Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	2	A
Power Dissipation T_a = 25 °C T_c = 25 °C	P_{tot}	1 10	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

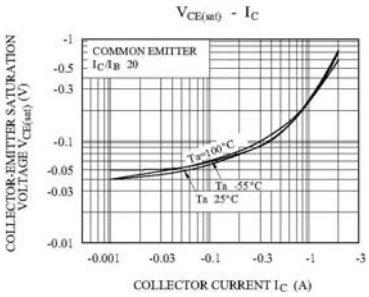
Characteristics at T_a = 25 °C

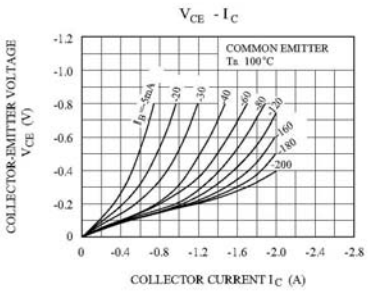
Parameter		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 2 V, $-I_C$ = 0.5 A Current Gain Group O Y at $-V_{CE}$ = 2 V, $-I_C$ = 1.5 A		h_{FE} h_{FE} h_{FE}	70 120 40	- - -	140 240 -	- - -
Collector Base Cutoff Current at $-V_{CB}$ = 50 V		$-I_{CBO}$	-	-	0.1	µA
Emitter Base Cutoff Current at $-V_{EB}$ = 5 V		$-I_{EBO}$	-	-	0.1	µA
Collector Emitter Breakdown Voltage at $-I_C$ = 10 mA		$-V_{(BR)CEO}$	50	-	-	V
Collector Emitter Saturation Voltage at $-I_C$ = 1 A, $-I_B$ = 0.05 A		$-V_{CE(sat)}$	-	-	0.5	V
Base Emitter Saturation Voltage at $-I_C$ = 1 A, $-I_B$ = 0.05 A		$-V_{BE(sat)}$	-	-	1.2	V
Transition Frequency at $-V_{CE}$ = 2 V, $-I_C$ = 0.5 A		f_T	-	100	-	MHz
Collector Output Capacitance at $-V_{CB}$ = 10 V, f = 1 MHz		C_{ob}	-	30	-	pF
Turn On Time at $-V_{CC}$ = 30 V, $-I_C$ = 1 A, $-I_{B1}$ = I_{B2} = 0.05 A, R_L = 30 Ω		t_{on}	-	0.1	-	µs
Storage Time at $-V_{CC}$ = 30 V, $-I_C$ = 1 A, $-I_{B1}$ = I_{B2} = 0.05 A, R_L = 30 Ω		t_{stg}	-	1	-	µs
Fall Time at $-V_{CC}$ = 30 V, $-I_C$ = 1 A, $-I_{B1}$ = I_{B2} = 0.05 A, R_L = 30 Ω		t_f	-	0.1	-	µs

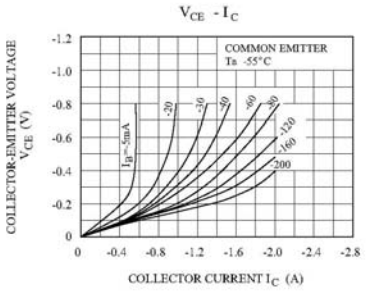
2SA1718R-HAF

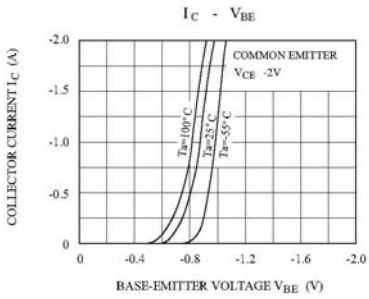


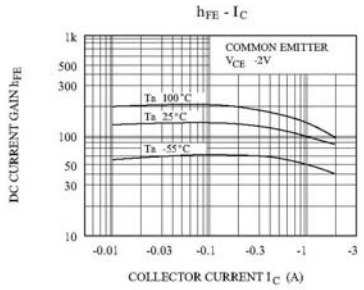


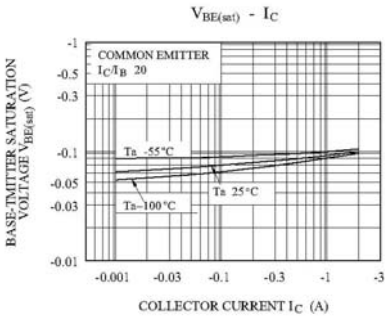


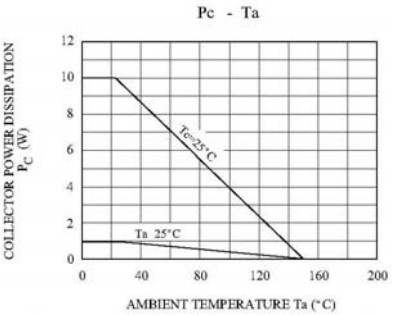






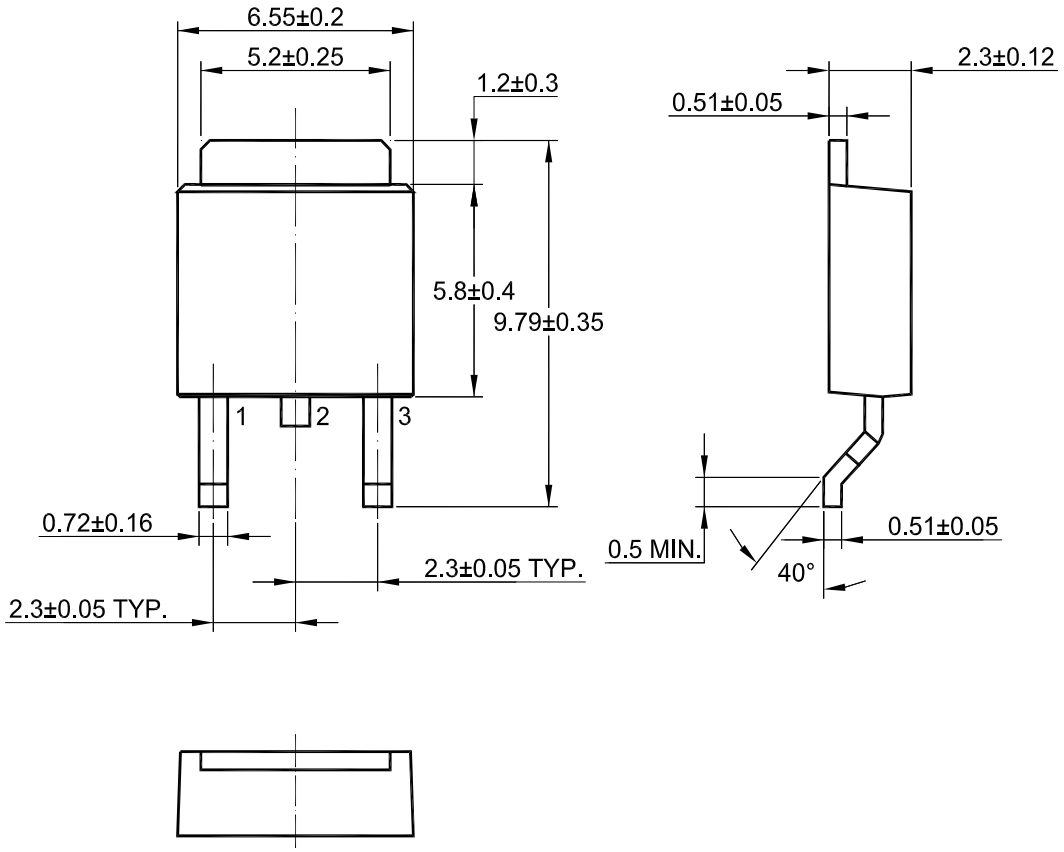






TOP DYNAMIC

TO-252 PACKAGE OUTLINE



Dimensions in mm